# Memory

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CS 3410, Spring 2015
Computer Science
Cornell University

See P&H Appendix B.8 (register files) and B.9

### **Announcements**

Make sure to go to <u>your</u> Lab Section this week
Completed Lab1 due *before* winter break, Friday, Feb 13th
Note, a <u>Design Document</u> is due when you submit Lab1 final circuit
Work <u>alone</u>

#### Save your work!

- Save often. Verify file is non-zero. Periodically save to Dropbox, email.
- Beware of MacOSX 10.5 (leopard) and 10.6 (snow-leopard)

#### Homework1 is out

Due a week before prelim1, Monday, February 23rd

Work on problems incrementally, as we cover them in lecture (i.e. part 1,

Office Hours for help

Work alone

#### Work alone, **BUT** use your resources

- Lab Section, Piazza.com, Office Hours
- Class notes, book, Sections, CSUGLab

### **Announcements**

### Check online syllabus/schedule

- http://www.cs.cornell.edu/Courses/CS3410/2015sp/schedule.html
- Slides and Reading for lectures
- Office Hours
- Pictures of all TAs
- Homework and Programming Assignments
- Dates to keep in Mind
  - Prelims: Tue Mar 3rd and Thur April 30th
  - Lab 1: Due next Friday, Feb 13th before Winter break
  - Proj2: Due Thur Mar 26th before Spring break
  - Final Project: Due when final would be (not known until Feb 14t

### Schedule is subject to change

## Collaboration, Late, Re-grading Policies

#### "Black Board" Collaboration Policy

- Can discuss approach together on a "black board"
- Leave and write up solution independently
- Do not copy solutions

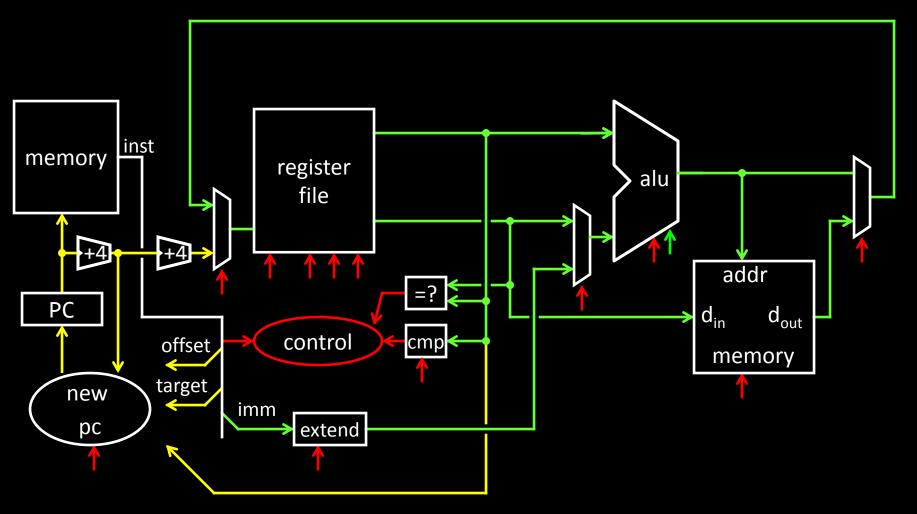
#### Late Policy

- Each person has a total of four "slip days"
- Max of two slip days for any individual assignment
- Slip days deducted first for any late assignment, cannot selectively apply slip days
- For projects, slip days are deducted from all partners
- <u>25%</u> deducted per day late after slip days are exhausted

#### Regrade policy

- Submit written request to lead TA,
   and lead TA will pick a different grader
- Submit another written request, lead TA will regrade directly
- Submit yet another written request for professor to regrade.

# Big Picture: Building a Processor



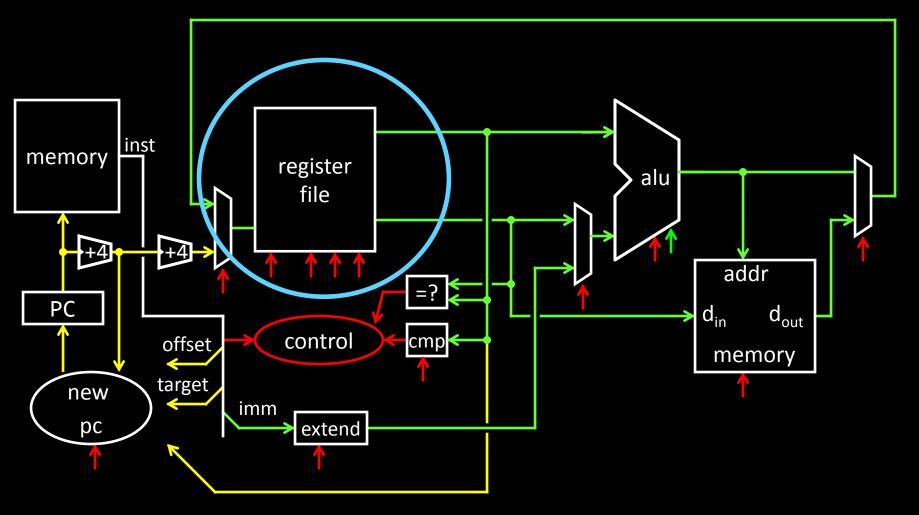
A Single cycle processor

# Goals for today

#### Memory

- Register Files
- Tri-state devices
- SRAM (Static RAM—random access memory)
- DRAM (Dynamic RAM)

# Big Picture: Building a Processor



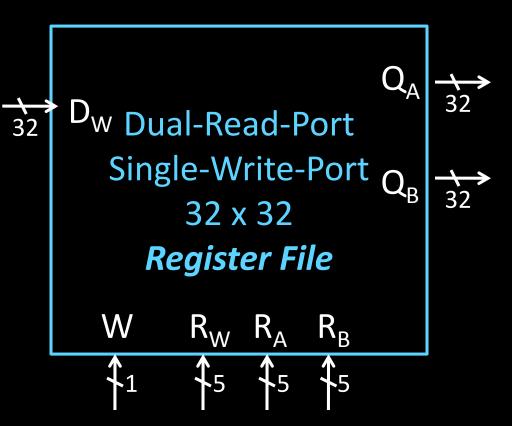
A Single cycle processor

# Register File

Register File

N read/write registers

Indexed by register number



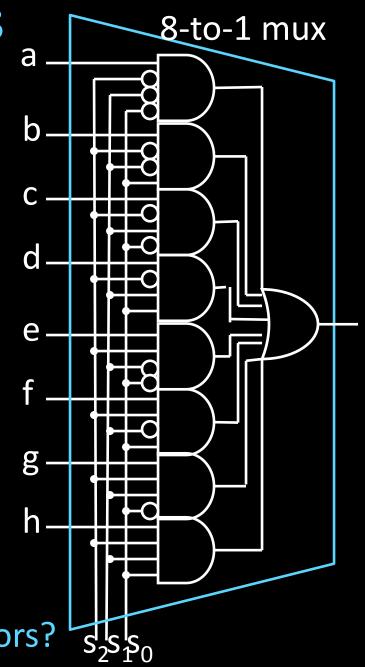
## **Tradeoffs**

### Register File tradeoffs

- + Very fast (a few gate delays for both read and write)
- + Adding extra ports is straightforward
- Doesn't scale
  e.g. 32Mb register file with
  32 bit registers
  Need 32x 1M-to-1 multiplexor

and 32x 20-to-1M decoder

How many logic gates/transistors?



## **Takeway**

Register files are very fast storage (only a few gate delays), but does not scale to large memory sizes.

## Goals for today

#### Memory

- CPU: Register Files (i.e. Memory w/in the CPU)
- Scaling Memory: Tri-state devices
- Cache: SRAM (Static RAM—random access memory)
- Memory: DRAM (Dynamic RAM)

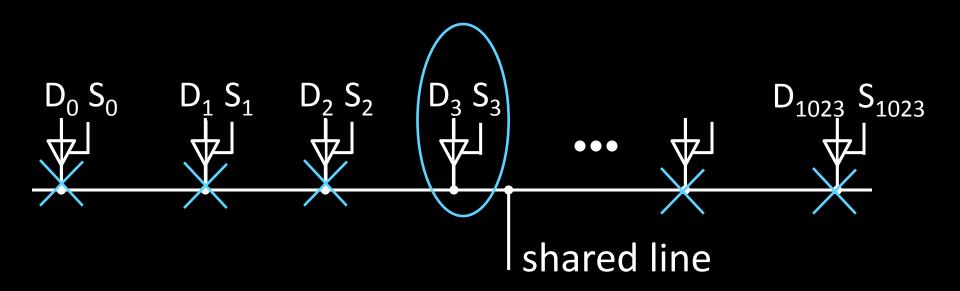
## **Next Goal**

How do we scale/build larger memories?

## **Building Large Memories**

Need a shared bus (or shared bit line)

- Many FlipFlops/outputs/etc. connected to single wire
- Only one output drives the bus at a time

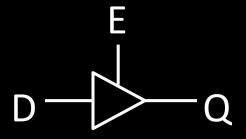


How do we build such a device?

## **Tri-State Devices**

#### **Tri-State Buffers**

- If enabled (E=1), then Q = D
- Otherwise, Q is not connected (z = high impedance)

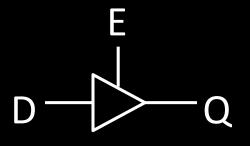


Ш	D	Q
0	0	Z
0	1	Z
1	0	0
1	1	1

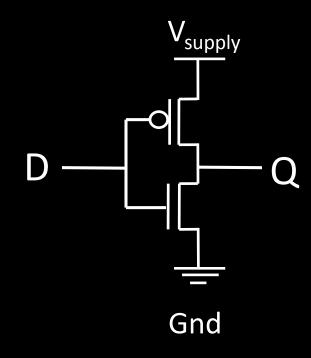
## **Tri-State Devices**

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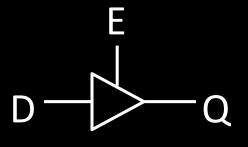
Ε	D	Q
0	0	Z
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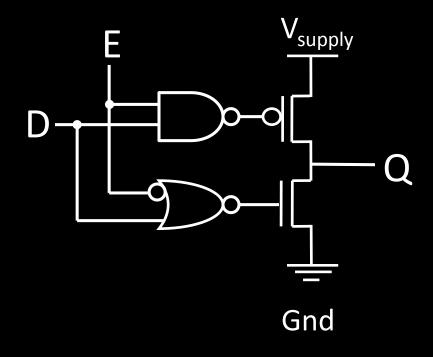
## **Tri-State Devices**

#### **Tri-State Buffers**

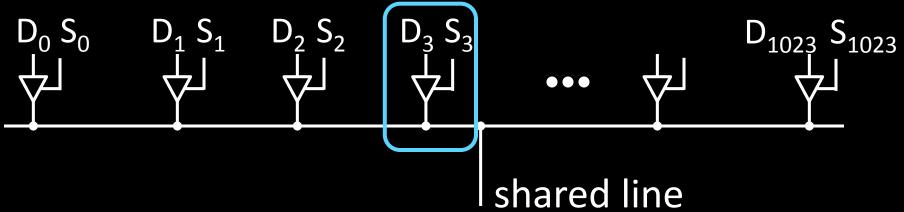
- If enabled (E=1), then Q = D
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ш	D	Q
0	0	Z
0	1	Z
1	0	0
1	1	1



# **Shared Bus**



## **Takeway**

Register files are very fast storage (only a few gate delays), but does not scale to large memory sizes.

Tri-state Buffers allow scaling since multiple registers can be connected to a single output, while only one register actually drives the output.

## Goals for today

#### Memory

- CPU: Register Files (i.e. Memory w/in the CPU)
- Scaling Memory: Tri-state devices
- Cache: SRAM (Static RAM—random access memory)
- Memory: DRAM (Dynamic RAM)

## **Next Goal**

How do we build large memories?

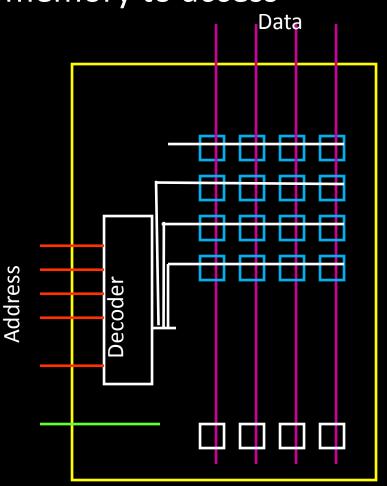
Use similar designs as Tri-state Buffers to connect multiple registers to output line. Only one register will drive output line.

## Static RAM (SRAM)—Static Random Access Memory

- Essentially just D-Latches plus Tri-State Buffers
- A decoder selects which line of memory to access

(i.e. word line)

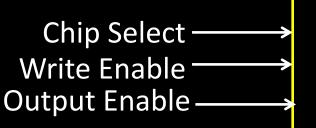
- A R/W selector determines the type of access
- That line is then coupled to the data lines



### Static RAM (SRAM)—Static Random Access Memory

- Essentially just D-Latches plus Tri-State Buffers
- A decoder selects which line of memory to access (i.e. word line)
- A R/W selector determines the 22
   type of access

  Address
- That line is then coupled to the data lines



SRAM 4M x 8



E.g. How do we design a 4 x 2 SRAM Module?

(i.e. 4 word lines that are each 2 bits wide)?

2 Address <del>\</del>

4 x 2 SRAM

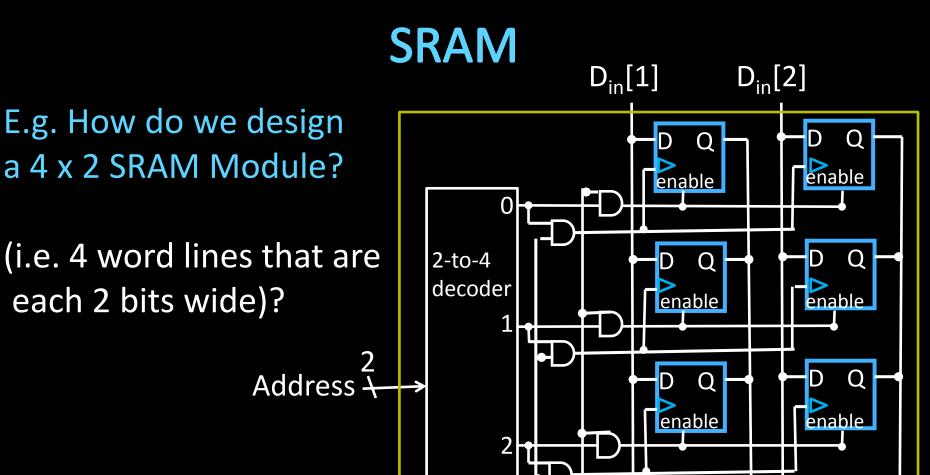
 $D_{in}[1]$ 

Write Enable — Output Enable —

 $D_{out}^{I}[1]$ 

 $D_{in}[2]$ 

 $D_{out}[2$ 



enable

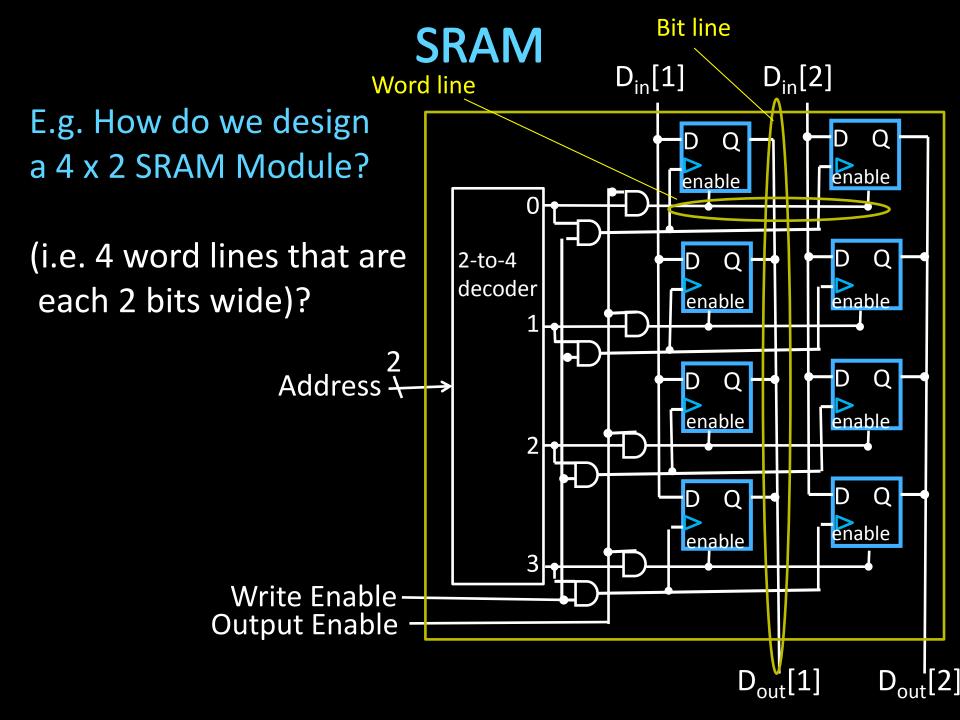
enable

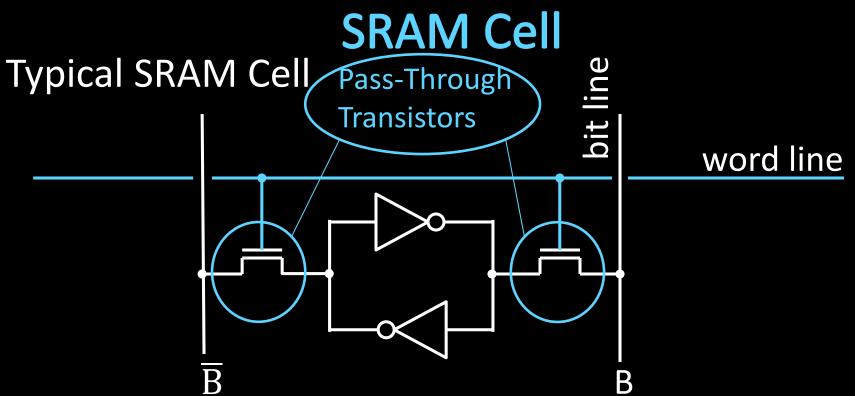
Write Enable-**Output Enable** 

E.g. How do we design

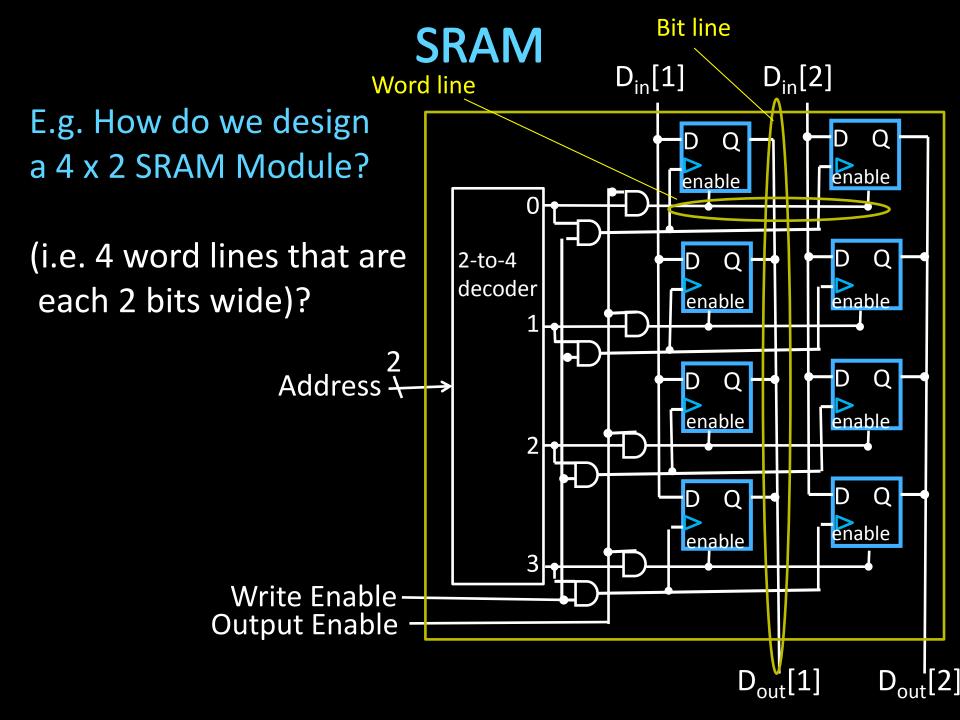
a 4 x 2 SRAM Module?

each 2 bits wide)?





Each cell stores one bit, and requires 4 – 8 transistors (6 is typical)





E.g. How do we design a 4 x 2 SRAM Module?

(i.e. 4 word lines that are each 2 bits wide)?

2 Address <del>\</del>

4 x 2 SRAM

 $D_{in}[1]$ 

Write Enable — Output Enable —

 $\mathsf{D}_\mathsf{out}^\mathsf{I}[1]$ 

 $D_{in}[2]$ 

 $D_{out}[2$ 

E.g. How do we design a **4M** x **8** SRAM Module?

(i.e. 4M word lines that are each 8 bits wide)?

22 Address <del>\</del>

Chip Select

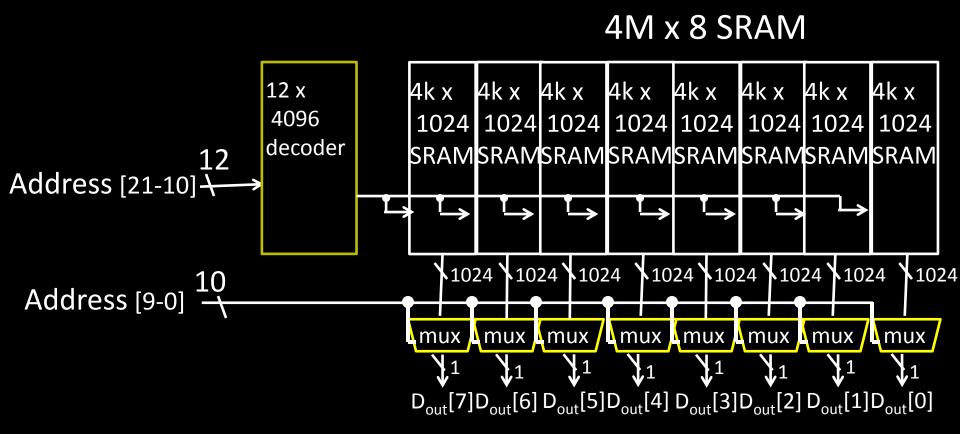
Write Enable — Output Enable —

 $D_{in} \downarrow 8$ 

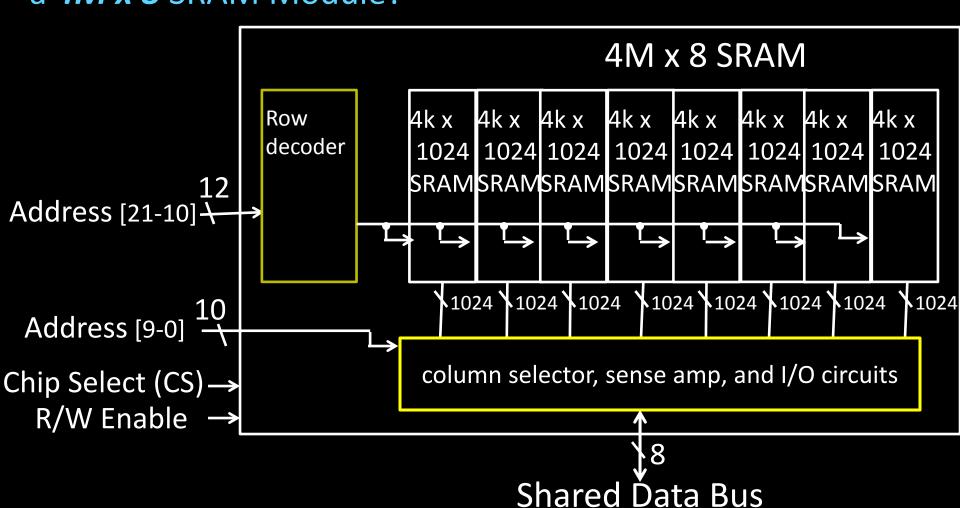
4M x 8 SRAM

 $D_{out}$   $\downarrow$  8

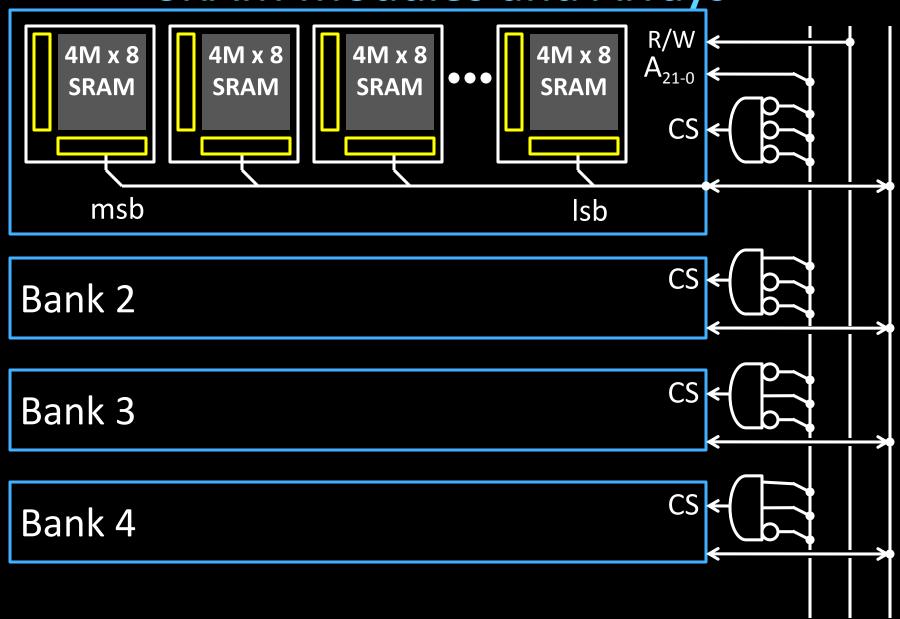
E.g. How do we design a **4M** x **8** SRAM Module?



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**SRAM Modules and Arrays** 



## **SRAM Summary**

#### **SRAM**

- A few transistors (~6) per cell
- Used for working memory (caches)

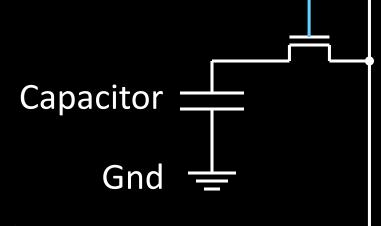
But for even higher density...

# **Dynamic RAM: DRAM**

## Dynamic-RAM (DRAM)

Data values require constant refresh

word line



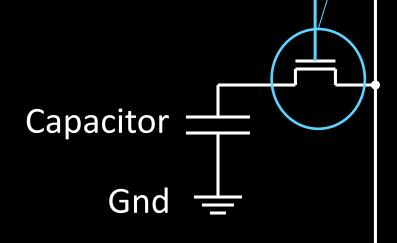
Each cell stores one bit, and requires 1 transistors

## Dynamic RAM: DRAM

Dynamic-RAM (DRAM) Transistors

Data values require constant refresh

word line



Each cell stores one bit, and requires 1 transistors

### DRAM vs. SRAM

#### Single transistor vs. many gates

- Denser, cheaper (\$30/1GB vs. \$30/2MB)
- But more complicated, and has analog sensing

#### Also needs refresh

- Read and write back...
- …every few milliseconds
- Organized in 2D grid, so can do rows at a time
- Chip can do refresh internally

Hence... slower and energy inefficient

# Memory

#### Register File tradeoffs

- Very fast (a few gate delays for both read and write)
- + Adding extra ports is straightforward
- Expensive, doesn't scale
- Volatile

#### Volatile Memory alternatives: SRAM, DRAM, ...

- Slower
- + Cheaper, and scales well
- Volatile

#### Non-Volatile Memory (NV-RAM): Flash, EEPROM, ...

- + Scales well
- Limited lifetime; degrades after 100000 to 1M writes

## Summary

We now have enough building blocks to build machines that can perform non-trivial computational tasks

Register File: Tens of words of working memory SRAM: Millions of words of working memory DRAM: Billions of words of working memory

NVRAM: long term storage (usb fob, solid state disks, BIOS, ...)

Next time we will build a simple processor!